(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property Organization
International Bureau

(43) International Publication Date
21 December 2000 (21.12.2000)

PCT

(10) International Publication Number
WO 00/77835 A1

(51) International Patent Classification[7]: H01L 21/00

(21) International Application Number: PCT/US00/14849

(22) International Filing Date: 30 May 2000 (30.05.2000)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
09/329,207 10 June 1999 (10.06.1999) US

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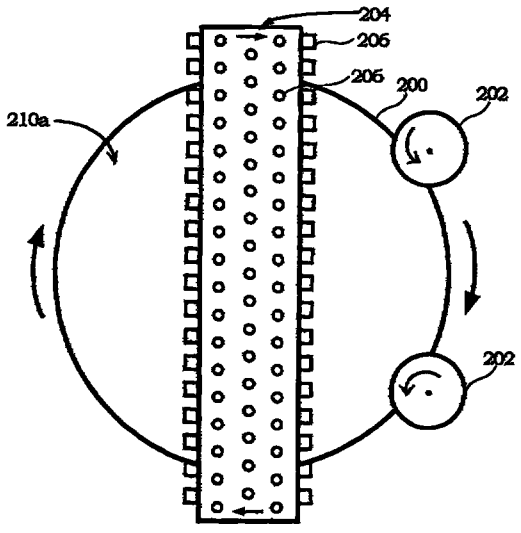
(81) Designated States *(national)*: AE, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BY, CA, CH, CN, CR, CU, CZ, DE, DK, DM, EE, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, NO, NZ, PL, PT, RO, RU, SD, SE, SG, SI, SK, SL, TJ, TM, TR, TT, TZ, UA, UG, UZ, VN, YU, ZA, ZW.

(84) Designated States *(regional)*: ARIPO patent (GH, GM, KE, LS, MW, MZ, SD, SL, SZ, TZ, UG, ZW), Eurasian patent (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European patent (AT, BE, CH, CY, DE, DK, ES, FI, FR, GB, GR, IE, IT, LU, MC, NL, PT, SE), OAPI patent (BF, BJ, CF, CG, CI, CM, GA, GN, GW, ML, MR, NE, SN, TD, TG).

Published:
— *With international search report.*

For two-letter codes and other abbreviations, refer to the "Guidance Notes on Codes and Abbreviations" appearing at the beginning of each regular issue of the PCT Gazette.

(54) Title: METHOD AND SYSTEM FOR CLEANING A SEMICONDUCTOR WAFER



(57) Abstract: A method and a system are provided for cleaning a surface of a wafer. The method starts by scrubbing the surface of the wafer with a cleaning brush that applies a chemical solution to the surface of the wafer. In one example, the cleaning brush implements a through the brush (TTB) technique to apply the chemicals. The scrubbing is generally performed in a brush box, with a top cleaning brush and a bottom cleaning brush. The top cleaning brush is then removed from contact with the surface of the wafer. The chemical concentration in the top brush may be maintained at substantially the same concentration that was in the brush during the scrubbing operation. Next, a flow of water (preferably de-ionized water) is delivered to the surface of the wafer. The delivery of water is preferably configured to remove substantially all of the chemical solution from the surface of the wafer before proceeding to a next cleaning operation.

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